

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
30	0.00325 at V _{GS} = 10 V	25	36
	0.0042 at V _{GS} = 4.5 V	22	

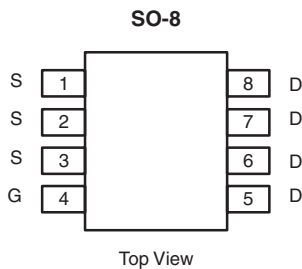
FEATURES

- Ultra Low On-Resistance Using High Density TrenchFET[®] Gen II Power MOSFET Technology
- Q_g Optimized
- 100 % R_g Tested

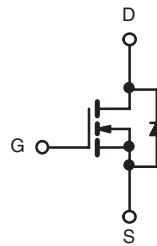


APPLICATIONS

- Synchronous Buck Low-Side
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier, POL



Ordering Information: Si4336DY-T1
Si4336DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	10 sec	Steady State	Unit	
Drain-Source Voltage	V _{DS}	30		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	25	17	A
		T _A = 70 °C	20	13	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	70			
Continuous Source Current (Diode Conduction) ^a	I _S	2.9	1.3		
Avalanche Current	I _{AS}	L = 0.1 mH	50		
Maximum Power Dissipation ^a		T _A = 25 °C	3.5	1.6	W
	T _A = 70 °C	2.2	1		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.0026	0.00325	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$		0.0033	0.0042	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		110		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\text{ A}, V_{GS} = 0\text{ V}$		0.72	1.1	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5600		μF
Output Capacitance	C_{oss}			860		
Reverse Transfer Capacitance	C_{rss}			415		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		36	50	nC
Gate-Source Charge	Q_{gs}			18		
Gate-Drain Charge	Q_{gd}			10		
Gate Resistance	R_g		0.8	1.3	2.0	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		24	35	ns
Rise Time	t_r			16	25	
Turn-Off Delay Time	$t_{d(off)}$			90	140	
Fall Time	t_f			32	50	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 2.9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	

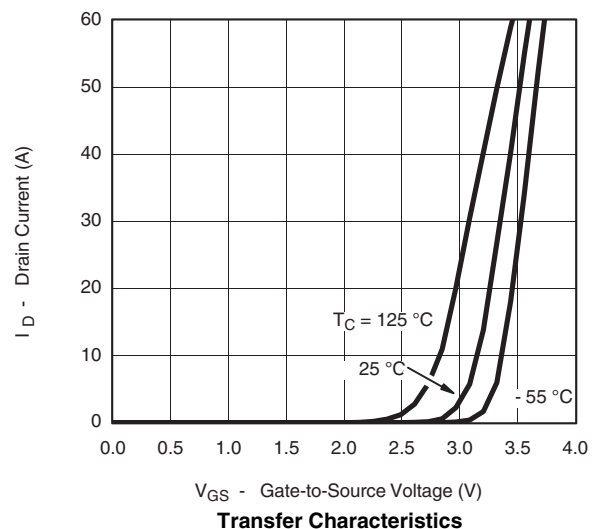
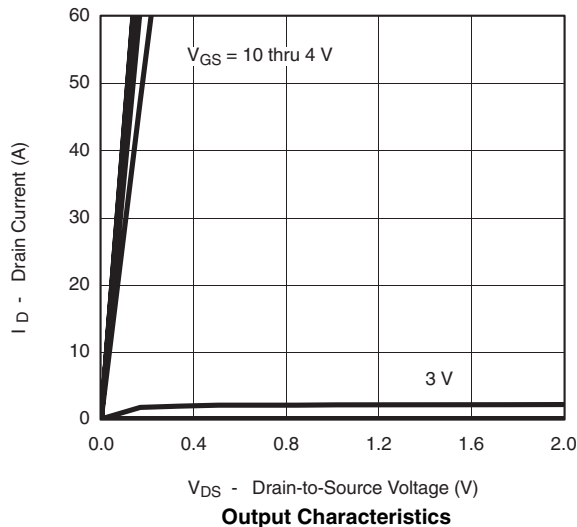
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

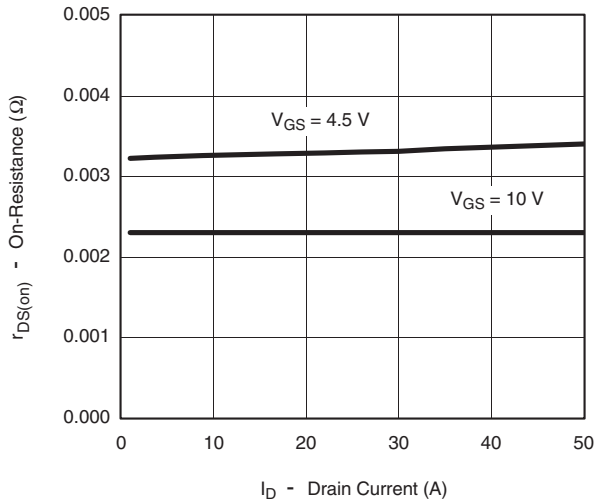
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

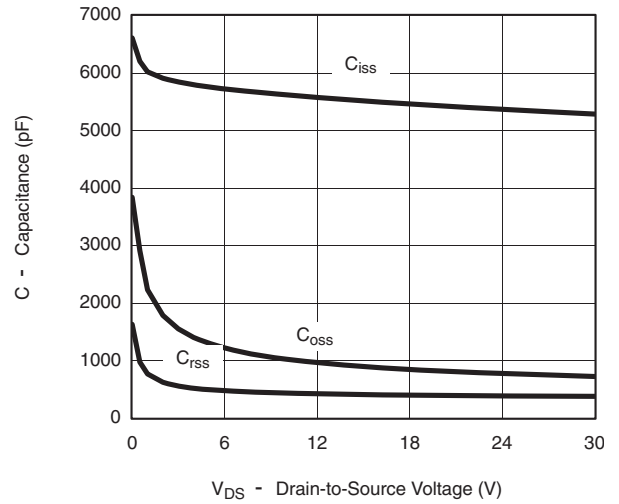
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



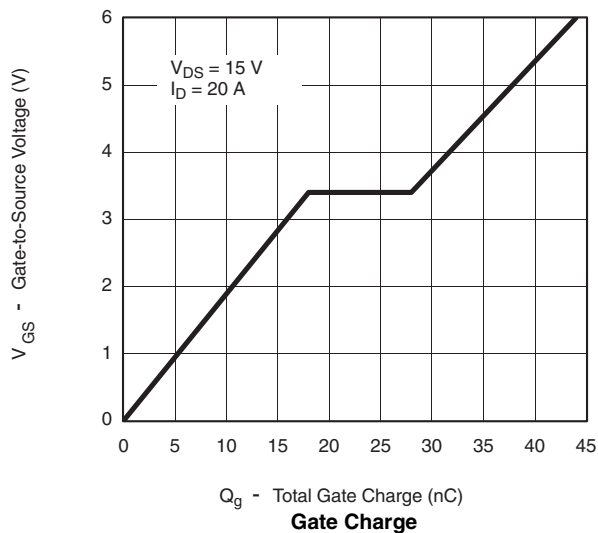
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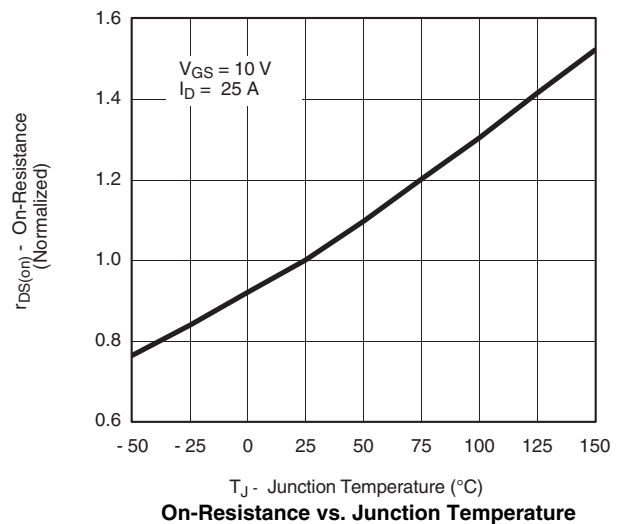
On-Resistance vs. Drain Current



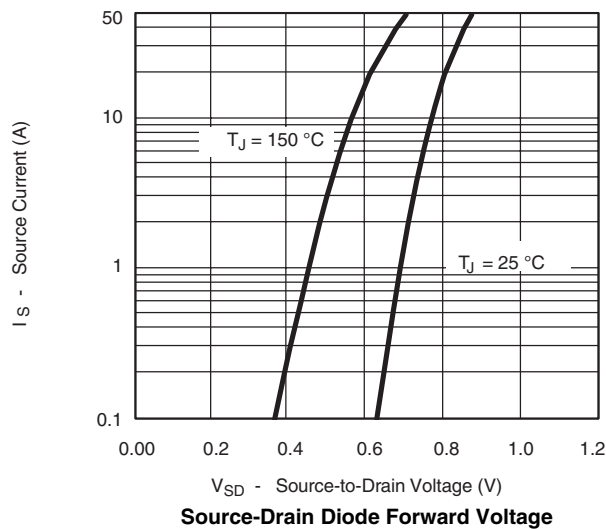
Capacitance



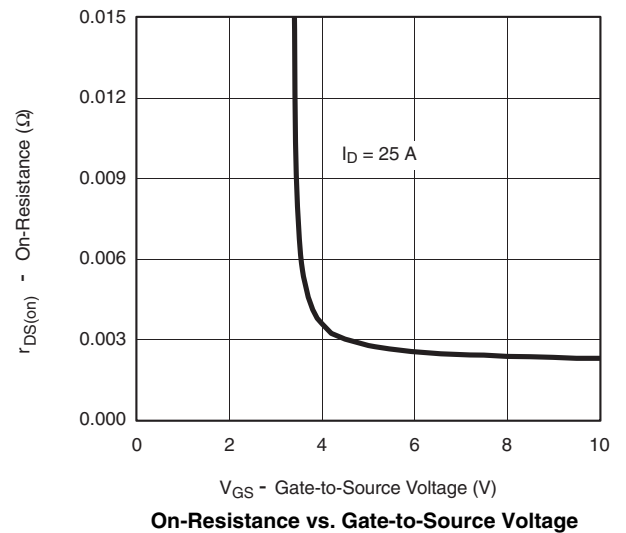
Gate Charge



On-Resistance vs. Junction Temperature

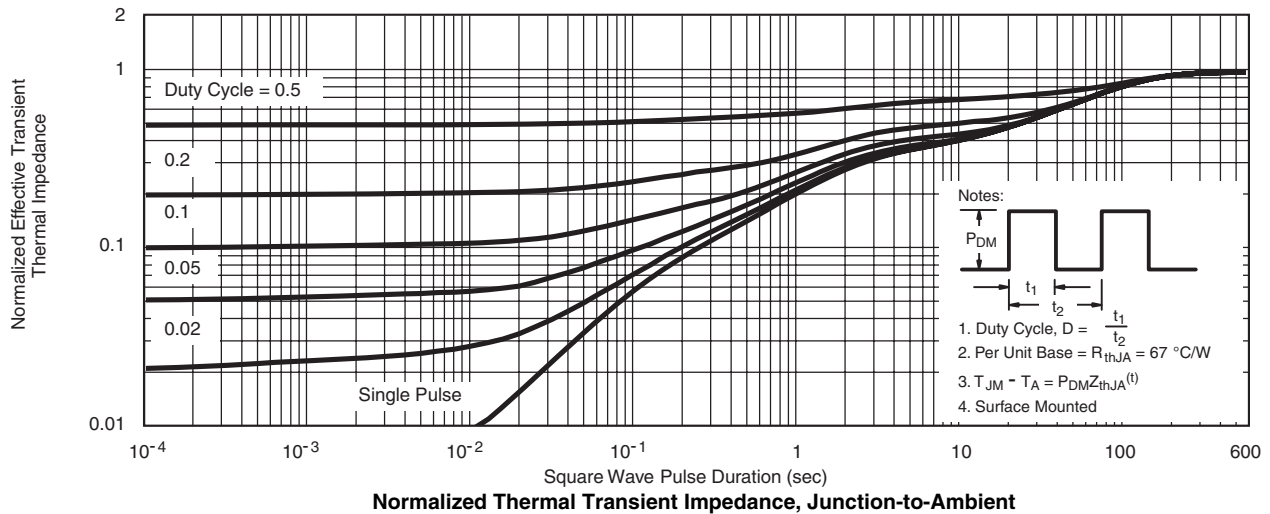
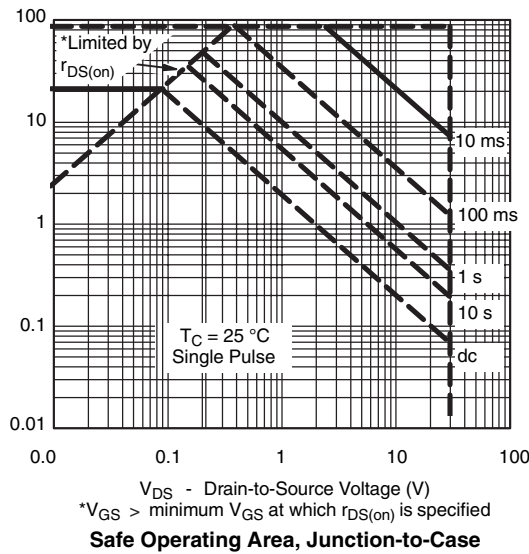
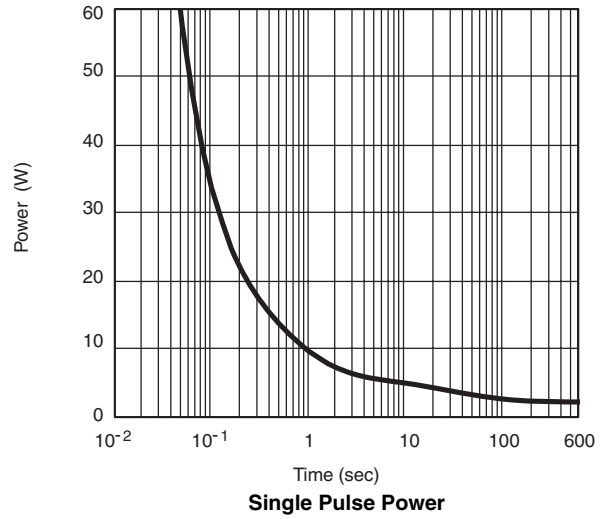
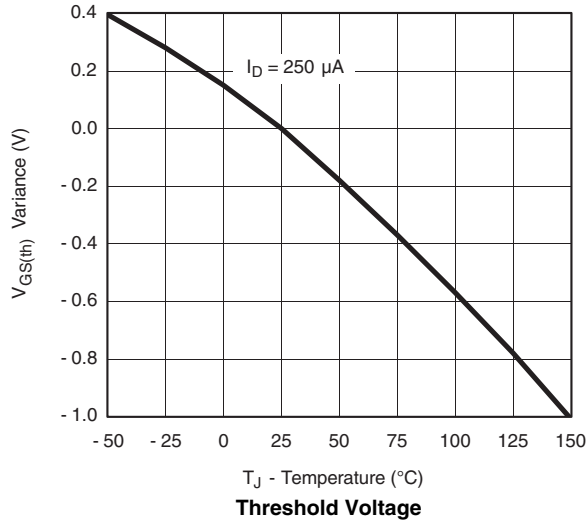


Source-Drain Diode Forward Voltage



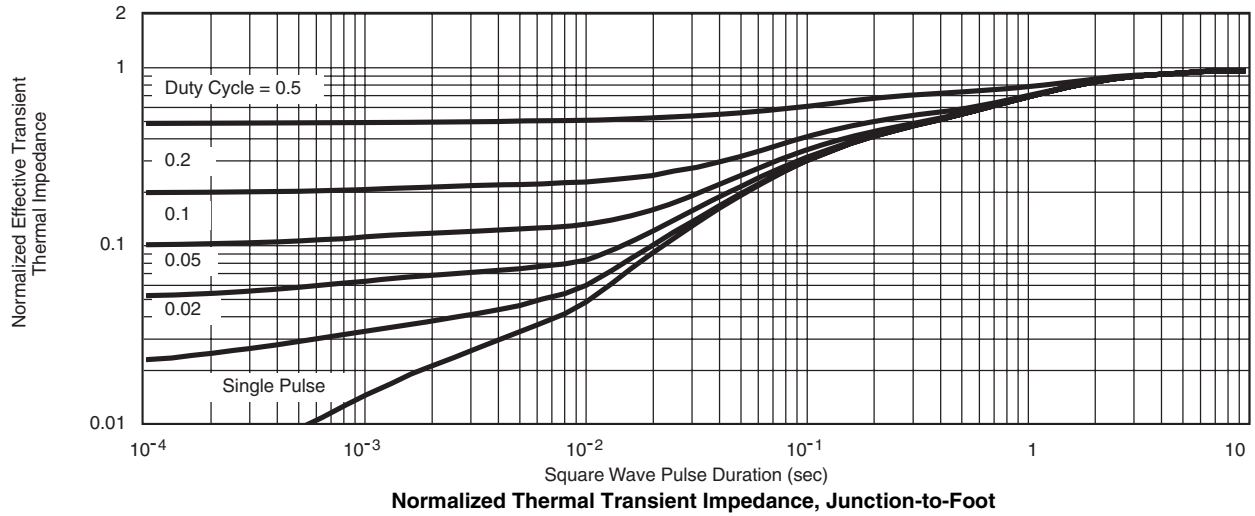
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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